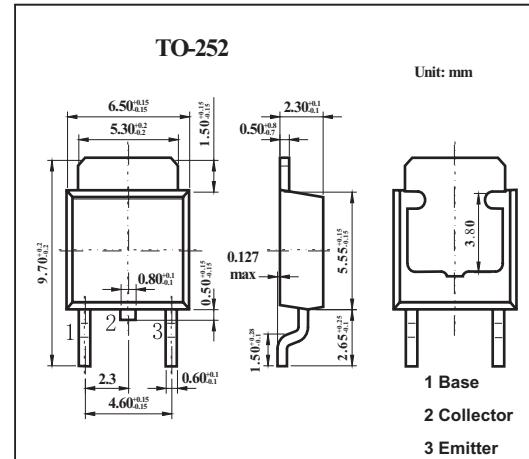


Silicon PNP Epitaxial Planar Type**2SB1070A****■ Features**

- Low collector-emitter saturation voltage $V_{CE(sat)}$.
- High-speed switching.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-4	A
Peak collector current	I_{CP}	-8	A
Collector power dissipation	P_C	1.3	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-emitter voltage	V_{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-40			V
Collector-base cutoff current	I_{CBO}	$V_{CB} = -50 \text{ V}, I_E = 0$			-50	μA
Emitter-base cutoff current	I_{EBO}	$V_{EB} = -5 \text{ V}, I_C = 0$			-50	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = -2 \text{ V}, I_C = -1 \text{ A}$	90		260	
		$V_{CE} = -2 \text{ V}, I_C = -0.1 \text{ A}$	45			
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -2 \text{ A}, I_B = -0.1 \text{ A}$			-1.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2 \text{ A}, I_B = -0.1 \text{ A}$			-0.5	V
Transition frequency	f_T	$V_{CE} = -5 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Turn-on time	t_{on}	$I_C = -2 \text{ A}, I_B1 = -0.2 \text{ A}, I_B2 = 0.2 \text{ A}, V_{CC} = -20 \text{ V}$		0.3		μs
Storage time	t_{stg}			0.4		μs
Fall time	t_f			0.1		μs

■ hFE Classification

Rank	Q	P
hFE	90~180	130~260